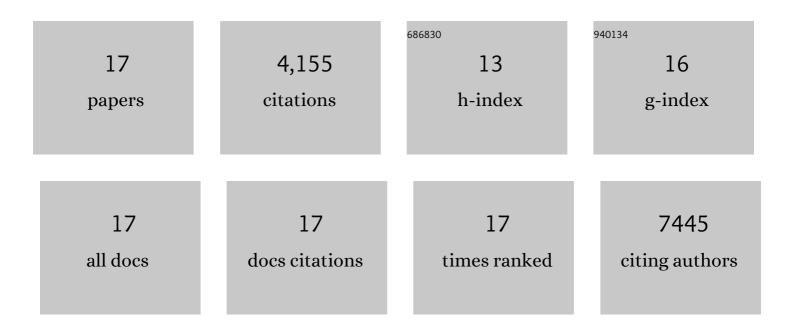
Sujay B Desai

List of Publications by Year in descending order

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SUIAV R DESAL

#	Article	IF	CITATIONS
1	MoS ₂ transistors with 1-nanometer gate lengths. Science, 2016, 354, 99-102.	6.0	1,140
2	Strong interlayer coupling in van der Waals heterostructures built from single-layer chalcogenides. Proceedings of the National Academy of Sciences of the United States of America, 2014, 111, 6198-6202.	3.3	970
3	Field-Effect Transistors Built from All Two-Dimensional Material Components. ACS Nano, 2014, 8, 6259-6264.	7.3	582
4	Strain-Induced Indirect to Direct Bandgap Transition in Multilayer WSe ₂ . Nano Letters, 2014, 14, 4592-4597.	4.5	572
5	Goldâ€Mediated Exfoliation of Ultralarge Optoelectronicallyâ€Perfect Monolayers. Advanced Materials, 2016, 28, 4053-4058.	11.1	307
6	Large-area and bright pulsed electroluminescence in monolayer semiconductors. Nature Communications, 2018, 9, 1229.	5.8	146
7	Monolithic 3D CMOS Using Layered Semiconductors. Advanced Materials, 2016, 28, 2547-2554.	11.1	107
8	MoS2 Heterojunctions by Thickness Modulation. Scientific Reports, 2015, 5, 10990.	1.6	93
9	Air stable <i>n</i> -doping of WSe2 by silicon nitride thin films with tunable fixed charge density. APL Materials, 2014, 2, .	2.2	76
10	Direct growth of single-crystalline III–V semiconductors on amorphous substrates. Nature Communications, 2016, 7, 10502.	5.8	45
11	Highly Sensitive Bulk Silicon Chemical Sensors with Sub-5 nm Thin Charge Inversion Layers. ACS Nano, 2018, 12, 2948-2954.	7.3	41
12	Spatially Precise Transfer of Patterned Monolayer WS ₂ and MoS ₂ with Features Larger than 10 ⁴ μm ² Directly from Multilayer Sources. ACS Applied Electronic Materials, 2019, 1, 407-416.	2.0	23
13	Ultrafast Spontaneous Emission from a Slot-Antenna Coupled WSe ₂ Monolayer. ACS Photonics, 2018, 5, 2701-2705.	3.2	17
14	Bright electroluminescence in ambient conditions from WSe2 p-n diodes using pulsed injection. Applied Physics Letters, 2019, 115, 011103.	1.5	13
15	2D layered materials: From materials properties to device applications. , 2015, , .		9
16	High-gain monolithic 3D CMOS inverter using layered semiconductors. Applied Physics Letters, 2017, 111, .	1.5	8
17	Gate Quantum Capacitance Effects in Nanoscale Transistors. Nano Letters, 2019, 19, 7130-7137.	4.5	6